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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/882,141	06/15/2001	Yiqiong Wang	AM1562D1 8856		
7	590 05/15/2002				
Patent Counsel			EXAMINER		
Applied Materials, Inc PO Box 450A			UMEZ ERONINI, LYNETTE T		
Santa Clara, CA 95052			ART UNIT	PAPER NUMBER	
			1765	8	
			DATE MAILED: 05/15/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

				AS-8				
		Application No.	Applicant(s)					
		09/882,141	WANG ET AL.4					
Office Action Summary		Examiner	Art Unit					
		Lynette T. Umez-Eronini	1765					
	The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. Insions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. Period for reply specified above is less than thirty (30) days, a repl period for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a rep y within the statutory minimum of thirty (will apply and will expire SIX (6) MONTH cause the application to become ABA	ly be timely filed 30) days will be considered timely 45 from the mailing date of this co	<i>f.</i> ommunication.				
1) 🗌	Responsive to communication(s) filed on	·						
2a)⊠	This action is FINAL. 2b) Th	is action is non-final.						
3) 🗌	3) Since this application is in condition for allowance except for formal matters, prosecution as to the ments is							
Dispositi	closed in accordance with the practice under ion of Claims	Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.					
4) 🖂	Claim(s) 1-6 is/are pending in the application.							
4a) Of the above claim(s) is/are withdrawn from consideration.								
5)⊠ Claim(s) <u>4</u> is/are allowed.								
6)⊠ Claim(s) <u>1-3,5 and 6</u> is/are rejected.								
7)	Claim(s) is/are objected to.							
•	Claim(s) are subject to restriction and/cion Papers	or election requirement.						
9) 🗌 🤈	The specification is objected to by the Examine	er.						
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.								
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.								
If approved, corrected drawings are required in reply to this Office action.								
12)	12)☐ The oath or declaration is objected to by the Examiner.							
Priority under 35 U.S.C. §§ 119 and 120								
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).								
a)	☐ All b)☐ Some * c)☐ None of:							
	1. Certified copies of the priority documen							
	2. Certified copies of the priority documen							
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 								
, -	14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).							
 a) The translation of the foreign language provisional application has been received. 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 								
Attachmen		573						
2) Notice	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of In	ummary (PTO-413) Paper No formal Patent Application (PT					
J.S. Patent and 1 PTO-326 (Re	Frademark Office ev. 04-01) Office A	ction Summary	Part o	of Paper No. 8				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1-3 are rejected under 35 U.S.C. 102(b) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Komura et al. (US 5,423,941) in view of Harshbarger et al (US 4,208,241).

In claim 1, lines 1-2, "for a silicon substrate connected to a low power bias source" is not given patentable weight because the claim recites functional language which tells intended use of rather than describe the invention.

Komura teaches etching a silicon semiconductor substrate with an etchant gas mixture comprising HBr, SiF₄, He, O₂, and SF₆ (Figure 1A; column 4 line 23-27; column 6, lines 49-52, 63-66; Tables 1, 2, 3, and 6; Figure 3; and column 4, lines 8-24).

Komura differs only in failing to teach an anisotropic etch mixture.

Harshbarger teaches anisotropic etching refers to etching resulting in an essentially flat, vertical etch wall on a plane approximately that of the initial resist edge prior to etching (column 4, lines 49-57), which is similar to Komura's trench in Fig **1A**.

Komura's etchant mixture provides a trench with a good configuration preserving a slight taper of trench side wall at an angle near 90° (column 2, lines 30-34, 52-57;

Tables 1, 2 and 6; and Figure **1A**). Since Komura's etchant mixture etches silicon to form a structure which has characteristics of an anisotropic etch as taught by Harshbarger, then it is the examiner's position that one having ordinary skill in the art at the time of the claimed invention would have found that using Komura's etchant mixture

would result in an anisotropic etch mixture consisting of at least one of the fluorine-containing gases selected from the group consisting of SF₆, Si₂F₆, and SiF₄; HBr and oxygen, as the claimed invention for the purpose of forming a trench having a good

configuration.

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 5 and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Komura '941) as applied to claim 1 above.

Komura differs only in failing to specify recited processing variables such as the volume ratio of HBr:SF₆ of 0.1 to 10, **in claim 5** and HBr and SF₆:O₂ of 0.1 to 10, **in claim 6**.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to employ any of a variety of processing variables such as those Art Unit: 1765

claimed by the applicant. They are well-known variables in the etching art and known to affect both the rate and quality of the etching process. Conducting routine experimentation for the purpose of obtaining the best-etched product would optimize the selection of a particular value. Changes in temperature, concentrations, or other process conditions of an old process do not impart patentability unless the recited ranges are critical, i.e., they produce a new and unexpected result. *In re Aller et al.*, 105 USPQ 233.

Allowable Subject Matter

5. Claim 4 is allowed. The following is a statement of reasons for the indication of allowable subject matter: Prior art fails to teach an etch mixture consisting essentially of a fluorine-containing gas that includes Si₂F₆ along with SF₆ and SiF₄; and HBr and oxygen.

Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the

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than SIX MONTHS from the date of this final action.

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shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 703-306-9074. The examiner can normally be reached on Second Friday.

Itue May 10, 2002 BENJAMIN L. UTECH SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 1700